**Product data sheet** 

## 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.





## 2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- Low forward voltage drop
- · Negligible switching losses
- High efficiency

## 3. Applications

- · DC to DC converters
- Freewheeling diode
- OR-ing diode

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			100			V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 129 °C; per diode; Fig. 1; Fig. 2; Fig. 3	20				А
$I_{O(AV)}$	average output current	$\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 127 °C; both diodes conducting	40				А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	$I_F = 5 \text{ A}$ ; $T_j = 25 ^{\circ}\text{C}$ ; per diode; Fig. 6		-	0.49	-	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>		-	0.43	-	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.73	0.78	V
		$I_F = 20 \text{ A}$ ; $T_j = 125 ^{\circ}\text{C}$ ; per diode; Fig. 6		-	0.67	0.71	V
I <sub>R</sub>	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7; Fig. 8$		-	-	50	μA
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; per diode; Fig. 7; Fig. 8		-	-	30	mA

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode		A1
3	A2	anode 2		K sym125
mb	К	mounting base; connected to cathode		3,11126

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN3S40100C	TO220	WN3S40100CQ	Tube	50	SOT78	13-Jun-2008

## 7. Marking

### Table 4. Marking codes

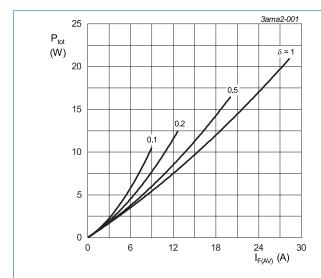
Type number	Marking codes
WN3S40100C	WN3S 40100C

## 8. Limiting values

#### Table 5. Limiting values

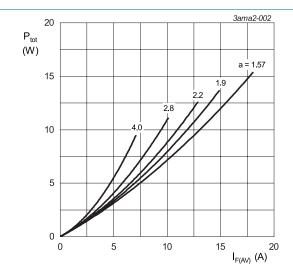
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		100	V
$V_{RWM}$	crest working reverse voltage		100	V
$V_R$	reverse voltage	DC	100	V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 129$ °C; per diode; Fig. 1; Fig. 2; Fig. 3	20	А
I <sub>O(AV)</sub>	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 127$ °C; both diodes conducting	40	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	330	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	363	А
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 0.541 \text{ V; } R_s = 0.0070 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor =  $I_{F(RMS)}$  /  $I_{F(AV)}$  V<sub>o</sub> = 0.541 V; R<sub>s</sub> = 0.0070  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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**Dual power Schottky diode** 

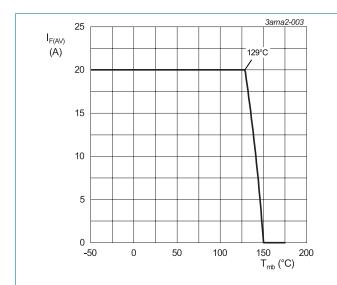


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

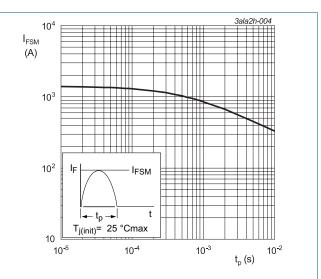


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

**Product data sheet** 

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	per diode; <u>Fig. 5</u>	-	-	1.3	K/W
	from junction to mounting base	both diodes conducting	-	-	0.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

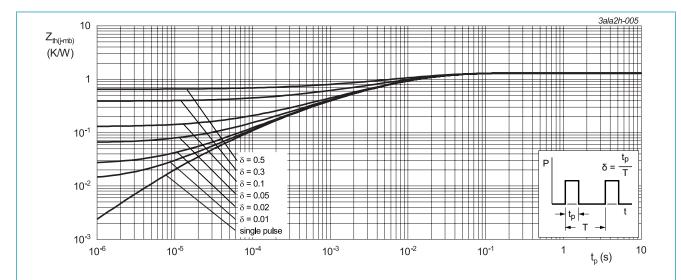
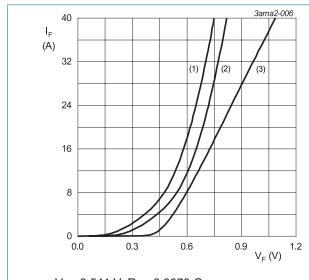


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Static cha	aracteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>	-	0.49	-	V		
				I <sub>F</sub> = 5 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>	-	0.43	-	V
				I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>	-	0.73	0.78	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>	-	0.67	0.71	V		
I <sub>R</sub>	reverse current	$V_R = 100 \text{ V; } T_j = 25 \text{ °C; per diode;}$ Fig. 7; Fig. 8	-	-	50	μA		
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; per diode; Fig. 7; Fig. 8	-	-	30	mA		



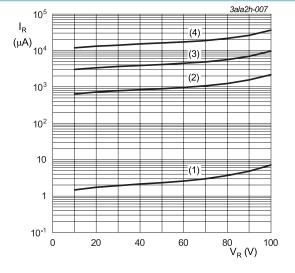
 $V_o = 0.541 \text{ V}; R_s = 0.0070 \Omega$ 

(1)  $T_j$  = 150 °C; typical values

(2) T<sub>j</sub> = 150 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



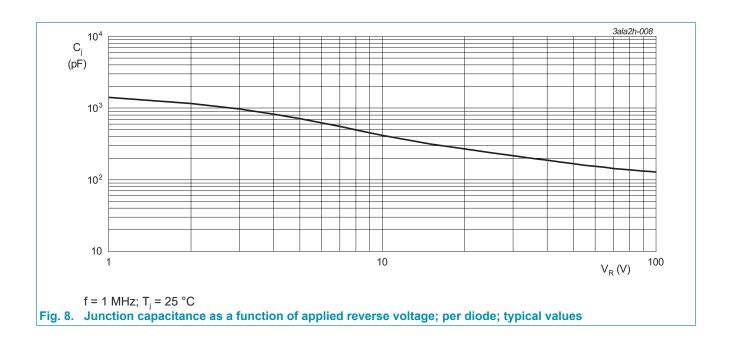
(1) T<sub>i</sub> = 25 °C; typical values

(2) T<sub>j</sub> = 100 °C; typical values

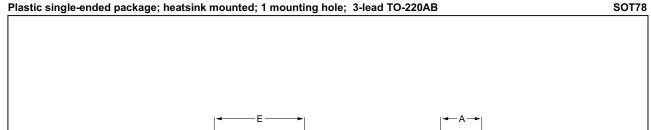
(3)  $T_j = 125 \,^{\circ}\text{C}$ ; typical values

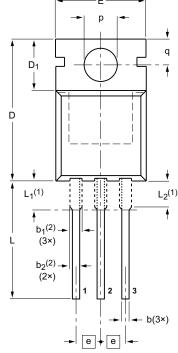
(4) T<sub>i</sub> = 150 °C; typical values

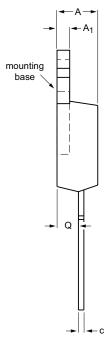
Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



# 11. Package outline







0 5 10 mm scale

### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE			REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	SION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT	Г78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**Dual power Schottky diode** 

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Date of release: 14 December 2021

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